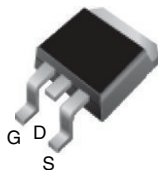


## Power MOSFET

**D<sup>2</sup>PAK (TO-263)**


N-Channel MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	60	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.018
$Q_g$ (Max.) (nC)	110	
$Q_{gs}$ (nC)	29	
$Q_{gd}$ (nC)	36	
Configuration	Single	

### FEATURES

- Advanced process technology
- Dynamic  $dV/dt$
- 175 °C operating temperature
- Fast switching
- Fully avalanche rated
- Drop in replacement of the IRFZ48, SiHFZ48 for linear / audio applications
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details



**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

### DESCRIPTION

Advanced power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>PAK is a surface-mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface-mount package. The D<sup>2</sup>PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2 W in a typical surface mount application.

### ORDERING INFORMATION

Package	D <sup>2</sup> PAK (TO-263)
Lead (Pb)-free and halogen-free	SiHFZ48RS-GE3
Lead (Pb)-free	IRFZ48RSPbF

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ °C}$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$V_{GS}$ at 10 V	$T_C = 25\text{ °C}$	A
		$T_C = 100\text{ °C}$	
Pulsed Drain Current <sup>a, e</sup>	$I_{DM}$	290	
Linear Derating Factor		1.3	W/°C
Single Pulse Avalanche Energy <sup>b, e</sup>	$E_{AS}$	100	mJ
Maximum Power Dissipation	$P_D$	190	W
Peak Diode Recovery $dV/dt$ <sup>c, e</sup>	$dV/dt$	4.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) <sup>d</sup>	For 10 s	300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 25\text{ V}$ , Starting  $T_J = 25\text{ °C}$ ,  $L = 22\text{ }\mu\text{H}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 72\text{ A}$  (see fig. 12)
- $I_{SD} \leq 72\text{ A}$ ,  $dI/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ °C}$
- 1.6 mm from case
- Current limited by the package, (die current = 72 A)

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.8	

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

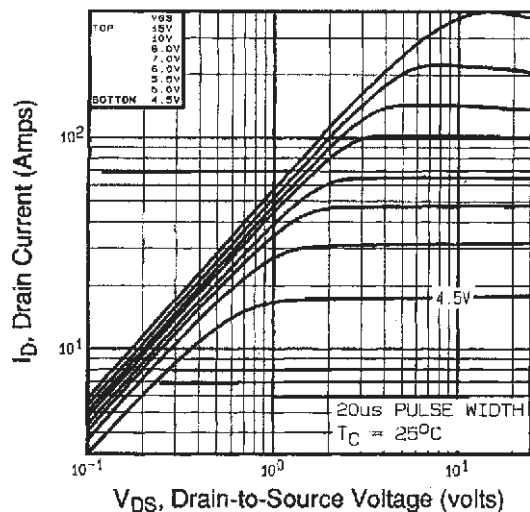
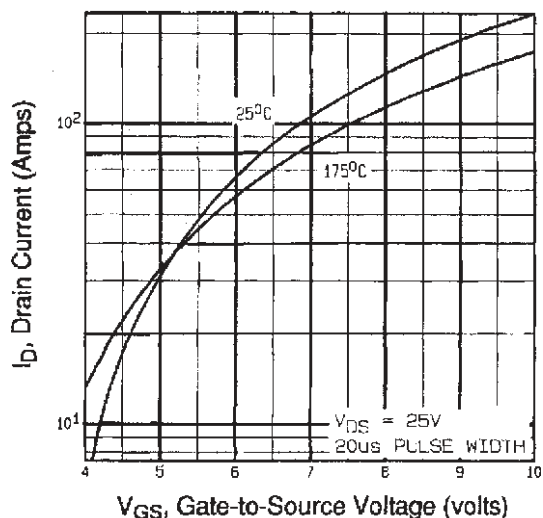
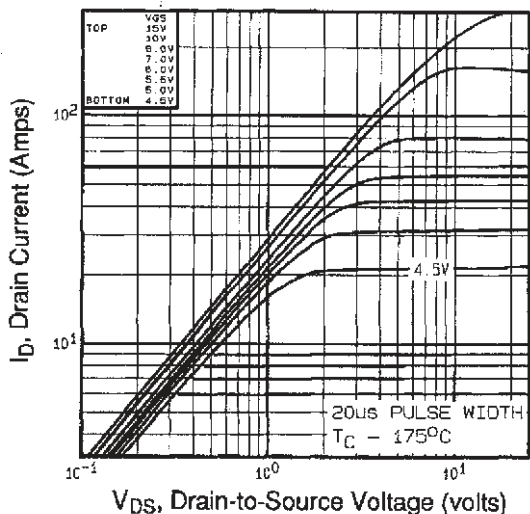
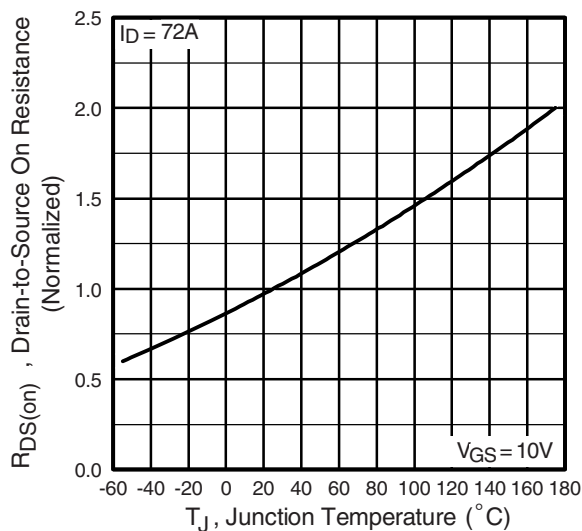
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		60	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA <sup>c</sup>		-	0.60	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V		-	-	25	μA
		V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C		-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 43 A <sup>b</sup>	-	-	0.018	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 43 A <sup>b</sup>		27	-	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5 <sup>c</sup>		-	2400	-	pF
Output Capacitance	C <sub>oss</sub>			-	1300	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	190	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 72 A, V <sub>DS</sub> = 48 V, see fig. 6 and 13 <sup>b, c</sup>	-	-	110	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	29	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	36	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 72 A, R <sub>g</sub> = 9.1 Ω, R <sub>D</sub> = 0.34 Ω, see fig. 10 <sup>b, c</sup>		-	8.1	-	ns
Rise Time	t <sub>r</sub>			-	250	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	210	-	
Fall Time	t <sub>f</sub>			-	250	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L <sub>S</sub>			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50 <sup>c</sup>	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	290	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 72 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	2.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 72 A, dI/dt = 100 A/μs <sup>b, c</sup>		-	120	180	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	0.50	0.80	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

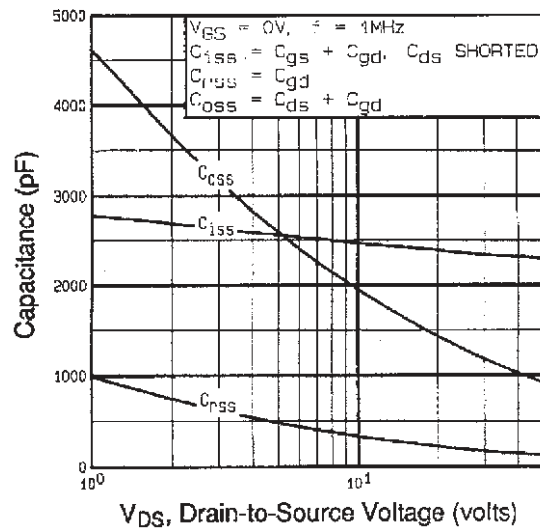
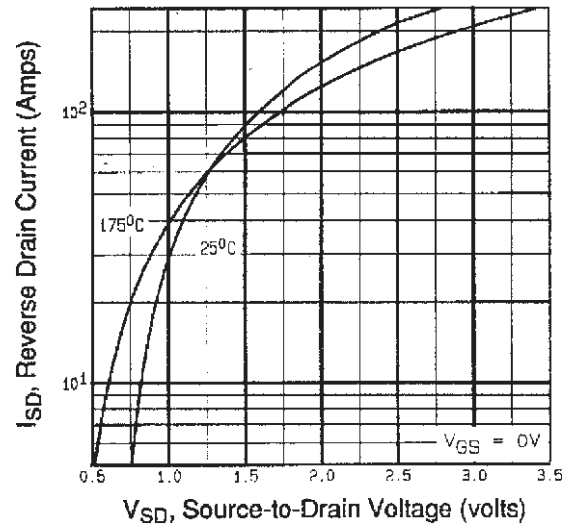
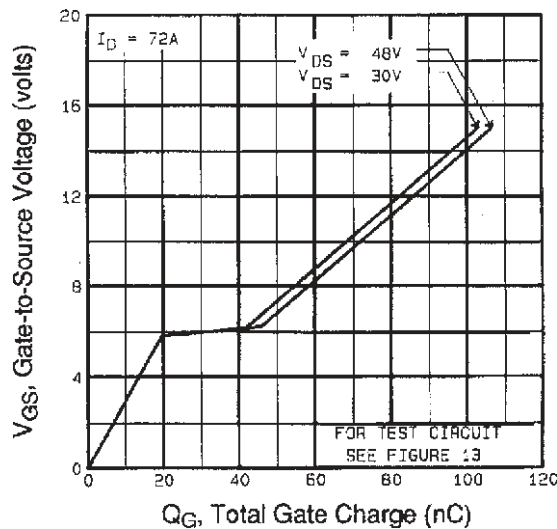
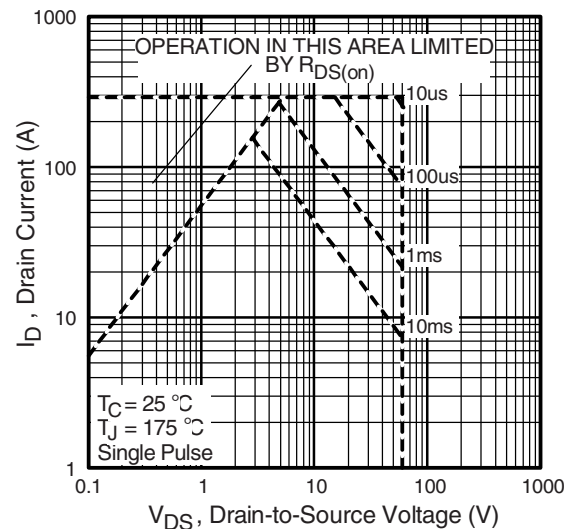
**Notes**

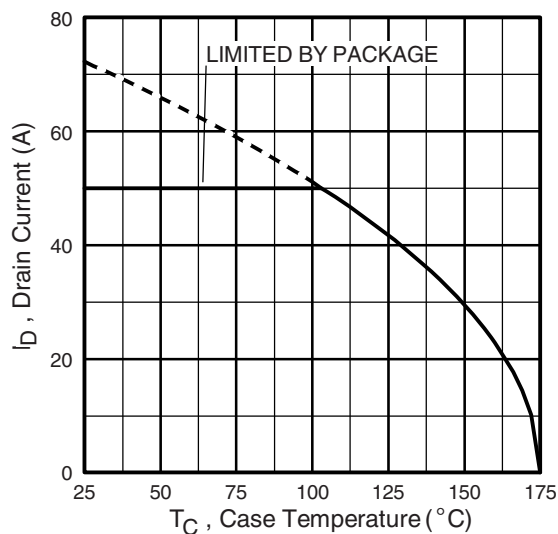
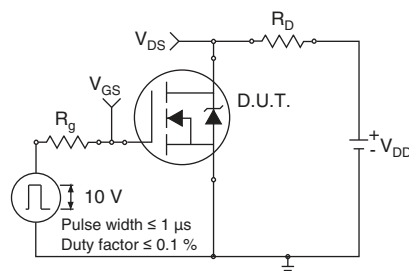
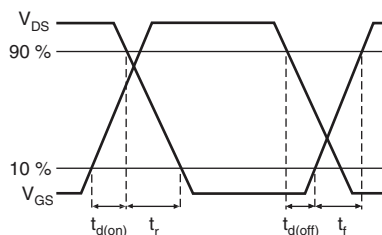
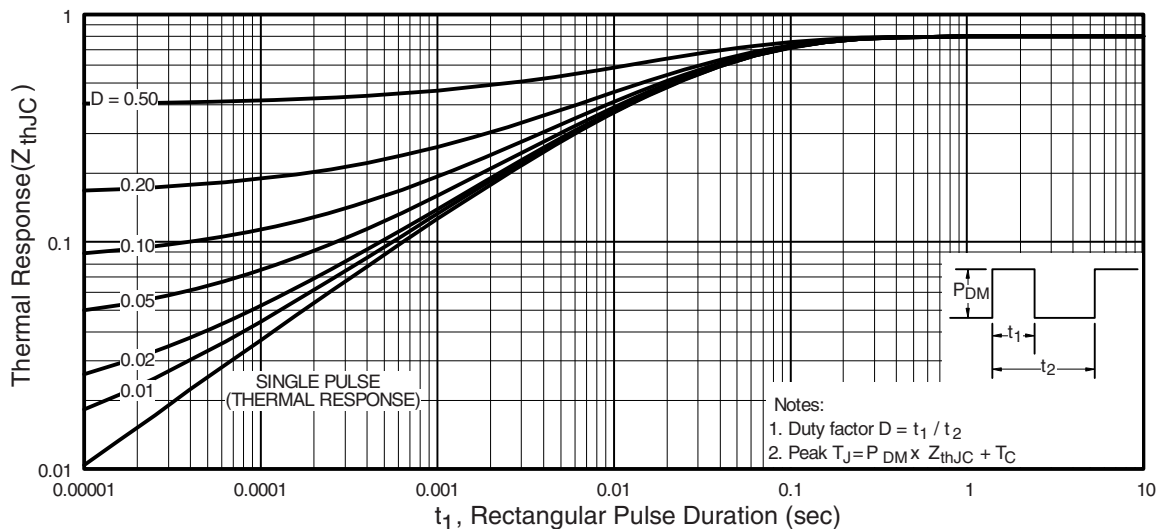
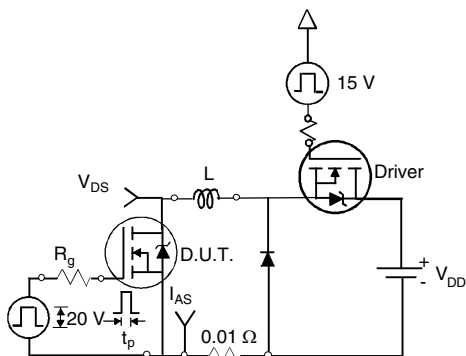
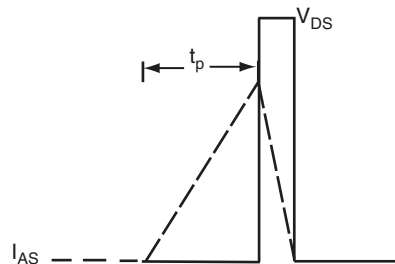
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

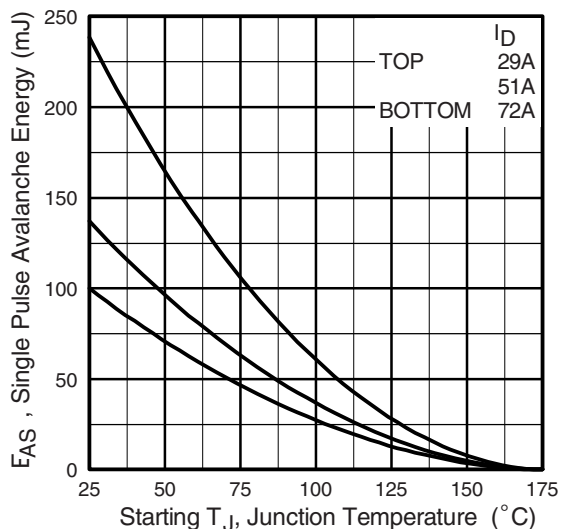
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ 

c. Current limited by the package, (die current = 72 A)

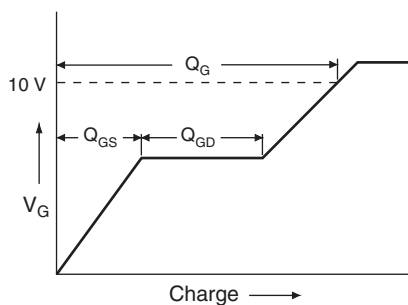
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 2 - Typical Transfer Characteristics**

**Fig. 1 - Typical Output Characteristics**

**Fig. 3 - Normalized On-Resistance vs. Temperature**


**Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 6 - Typical Source-Drain Diode Forward Voltage**

**Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 7 - Maximum Safe Operating Area**

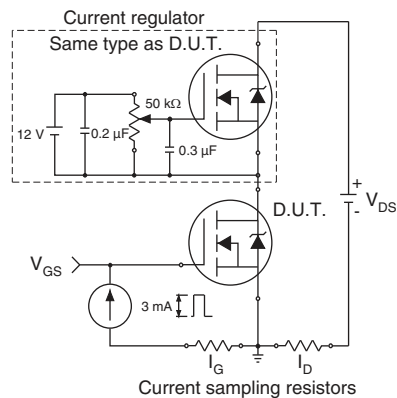

**Fig. 8 - Maximum Drain Current vs. Case Temperature**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig. 12a - Unclamped Inductive Test Circuit**

**Fig. 12b - Unclamped Inductive Waveforms**



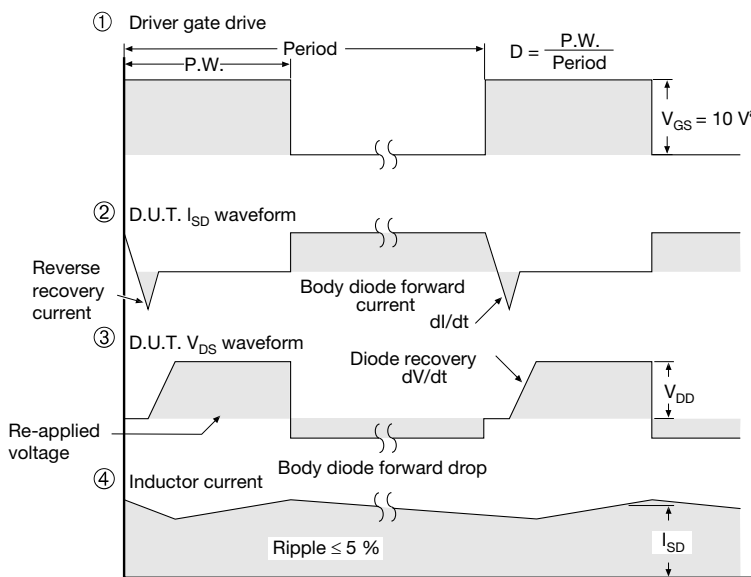
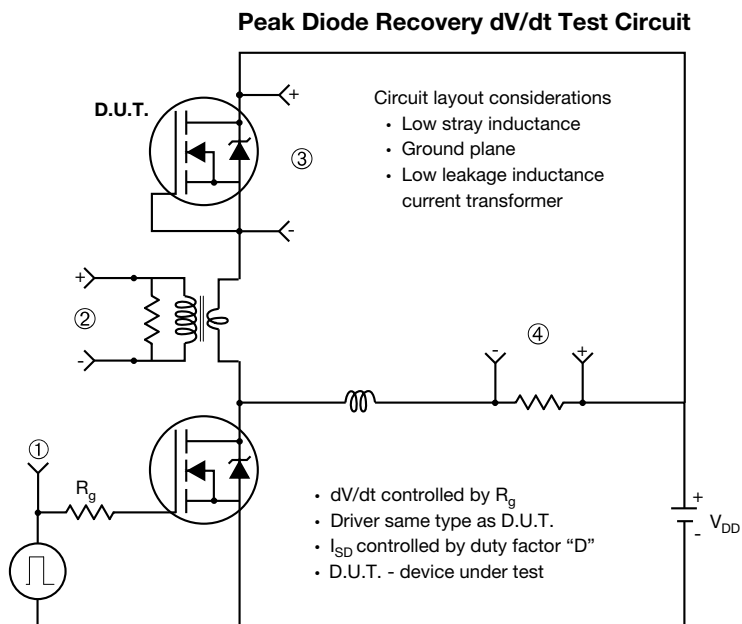
**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**



**Fig. 13a - Maximum Avalanche Energy vs. Drain Current**



**Fig. 13b - Gate Charge Test Circuit**

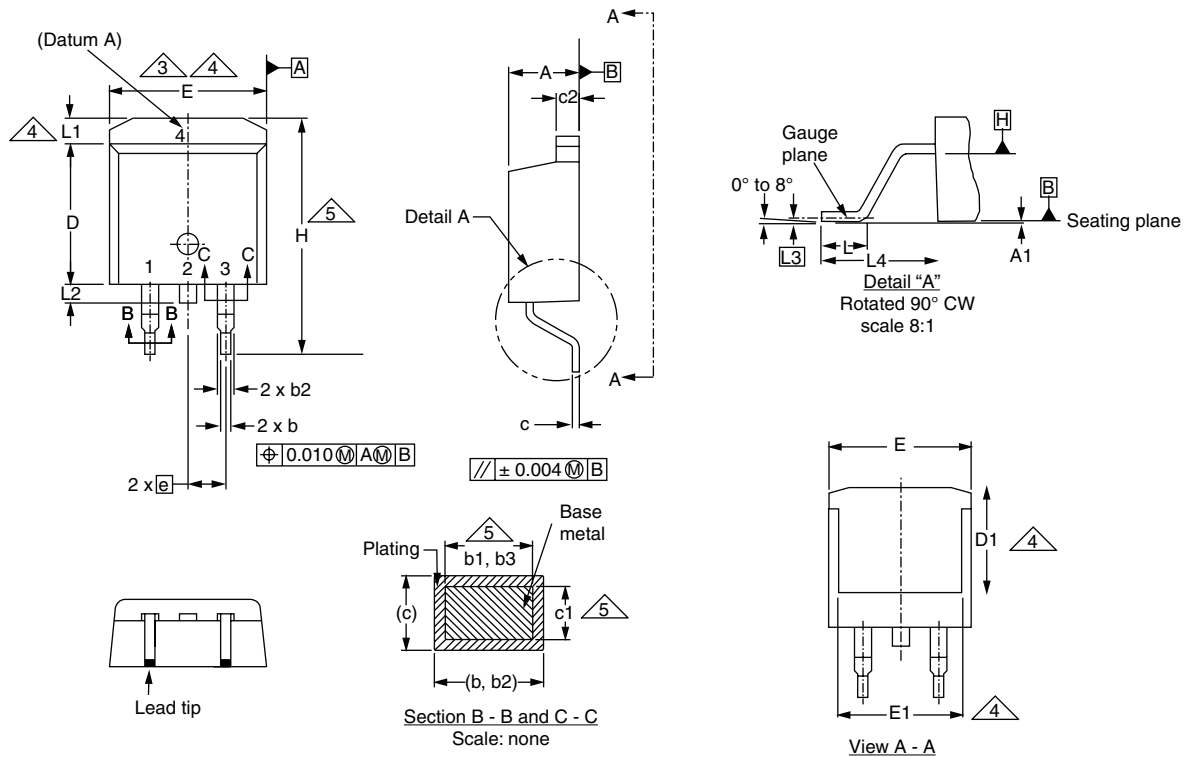

**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 10 - For N-Channel**

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### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

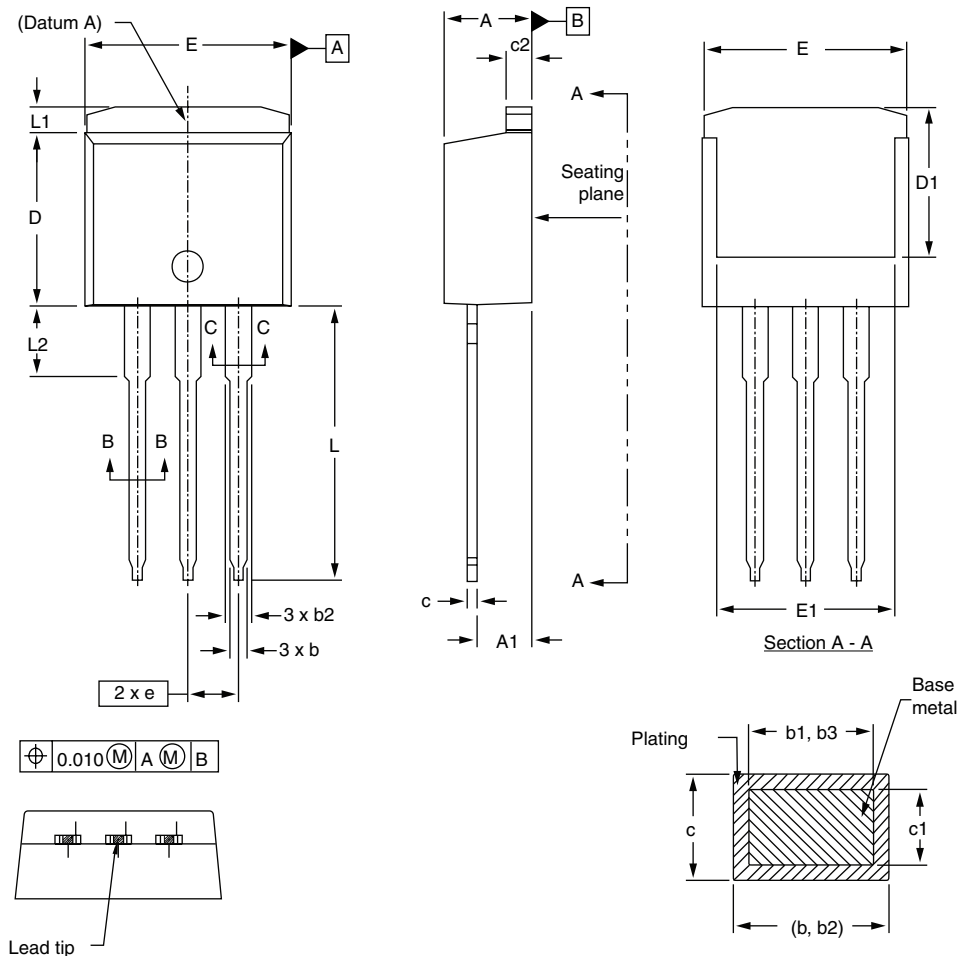
ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



## I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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